ADVANCED POWER TECHNOLOGY RF®

MMBR911LT1

RF & MICROWAVE TRANSISTORS

DESCRIPTION

The MMBR911LT1 is a low noise, high gain, discrete silicon bipolar transistors housed in low cost plastic packages.

IMPORTANT: For the most current data, visit: ***http://www.advancedpower.com***

KEY FEATURES

- High FTau-6.0 GHz
- Low noise-2.9dB@1GHz
- Low cost SOT23 package

APPLICATIONS/BENEFITS

- LNA, Oscillator, Pre-Driver

ABSOLUTE MAXIMUM RATINGS (T_{CASE} = 25°C)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	20	V
V_{CEO}	Collector-Emitter Voltage	12	V
V_{EBO}	Emitter-Base Voltage	2.0	V
I_C	Device Current	60	mA
P_{DISS}	Power Dissipation	333	mW
T_J	Junction Temperature	150	C
T_{STG}	Storage Temperature	-55 to +150	C

SOT-23
MMBR911LT1

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	225	C/W

STATIC ELECTRICAL SPECIFICATIONS (TCASE = 25°C)

Symbol	Test Conditions		Min.	Typ.	Max.	Units
BV_{CBO}	I_C = .1mA	I_E = 0	20			V
BV_{CEO}	I_C =1.0mA	I_B = 0	12			V
I_{CBO}	V_{CB} =15V	I_E = 0			50	nA
h_{FE}	V_{CE} =10V	I_C = 30mA	30		200	

DYMANIC ELECTRICAL SPECIFICATIONS (TCASE = 25°C)

Symbol	Test Conditions	Min.	Typ.	Max.	Units
C_{CB}	V_{CB} = 10 V **f** = 1.0 MHz		1.0		pF
FTau	V_{CE} = 10 V Ic= 30 mA **f** = 1.0 GHz		6.0		GHz
NFmin	V_{CE} = 10 V Ic= 10 mA **f** = 1.0 GHz		2.9		dB
G_{NF}	V_{CE} = 10 V Ic= 10 mA **f** = 1.0 GHz		11		dB